Search History (11pp.) [illegible] (11/14/05)

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|---|---|---|---|---|---|---|
| L1 | 117 | MQW near6 efficiency | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 08:58 |
| L2 | 0 | MQW near6 efficiency near6 light adj emitting and LED.ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 08:58 |
| L3 | 7 | MQW near6 efficiency near6 light adj emitting | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 08:58 |
| L4 | 20 | MQW near6 efficiency near6 ("LED" light adj emitting) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 09:49 |
| L5 | 11454 | ((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/11/14 09:49 |
| L6 | 12220 | ((257/79) or (257/8$1) or (257/9$1) or (257/100) or (257/101) or (257/102) or (257/103) or (372/43.01)).CCLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/11/14 09:49 |
| L7 | 124 | 6 and (damag$3 exfoliat$3 degradat$3 erosion eroding corrosion corroding) near6 electrode and transparent near4 electrode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 09:52 |
| L8 | 83 | 6 and (damag$3 exfoliat$3 degradat$3 erosion eroding corrosion corroding) near6 electrode and transparent near4 electrode and @ad<"20030401" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 09:52 |
| S1 | 5 | "807413".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/30 18:43 |

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| S2 | 2 | jp-2002226846$-$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/30 19:06 |
| S3 | 41 | exfoliati$2.ti,ab,clm. and (light-emitting adj (device diode) light adj emitting adj (device diode)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:12 |
| S4 | 3 | exfoliati$2.ti,ab,clm. and (light-emitting adj (device diode) light adj emitting adj (device diode)) and AlGaAs and (ITO indium-tin-oxide) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:20 |
| S5 | 1 | exfoliati$2 near6 AlGaAs and (ITO indium-tin-oxide) and (257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:22 |
| S6 | 1 | exfoliati$2 near6 AlGaAs and (ITO indium-tin-oxide) and (372/4$1.ccls. 372/50.ccls. 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:22 |
| S7 | 2 | (lift-off exfoliati$2) near6 AlGaAs and (ITO indium-tin-oxide) and (372/4$1.ccls. 372/50.ccls. 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:24 |
| S8 | 5 | (lift-off exfoliati$2) near6 (aluminum AlGaAs) and (ITO indium-tin-oxide) and (372/4$1.ccls. 372/50.ccls. 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:26 |
| S9 | 1 | (exfoliati$2) near6 (aluminum AlGaAs)and (372/4$1.ccls. 372/50.ccls. 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:26 |
| S10 | 1 | (exfoliati$2) near6 (aluminum AlGaAs) and (372/4$1.ccls. 372/50.ccls. 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:26 |
| S11 | 1 | (exfoliati$2) near6 (aluminum AlGaAs Al AlAs) and (372/4$1.ccls. 372/50.ccls. 257/79.ccls. 257/8$1.ccls. 257/9$1.ccls. 257/10$1.ccls.) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:27 |

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| S12 | 131 | (exfoliati$2) near6 aluminum | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:29 |
| S13 | 68 | (exfoliati$2) near3 aluminum | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:34 |
| S14 | 19 | (ITO indium-tin-oxide) near6 (AlGaAs AlAs) and ((light-emitting light adj emitting) adj (diode device laser)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:03 |
| S15 | 1259 | stop adj layer.ti. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:49 |
| S16 | 2 | stop adj layer.ti. and light-emitting adj diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 19:49 |
| S17 | 0 | (ITO indium-tin-oxide) near6 (AlGaAs:Zn AlGaAs:Si AlGaAs:Ge AlAs:Zn AlAs:Si AlGa:Ge) and ((light-emitting light adj emitting) adj (diode device laser)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:04 |
| S18 | 0 | (ITO indium-tin-oxide) near6 ("AlGaAs:Zn" "AlGaAs:Si" "AlGaAs:Ge" "AlAs:Zn" "AlAs:Si" "AlGa:Ge") and ((light-emitting light adj emitting) adj (diode device laser)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:04 |
| S19 | 0 | (ITO indium-tin-oxide) near6 (AlGaAs near4 ((heavily highly) adj doped) "AlGaAs:Zn" "AlGaAs:Si" "AlGaAs:Ge" "AlAs:Zn" "AlAs:Si" "AlGa:Ge") and ((light-emitting light adj emitting) adj (diode device laser)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:05 |
| S20 | 0 | (ITO indium-tin-oxide) near10 (AlGaAs near4 ((heavily highly) adj doped) "AlGaAs:Zn" "AlGaAs:Si" "AlGaAs:Ge" "AlAs:Zn" "AlAs:Si" "AlGa:Ge") and ((light-emitting light adj emitting) adj (diode device laser)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:06 |

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| S21 | 17 | (ITO indium-tin-oxide) near10 AlGaAs and (light-emitting light adj emitting) adj diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:06 |
| S22 | 0 | (ITO indium-tin-oxide) near10 AlGaAs:Zn and (light-emitting light adj emitting) adj diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:06 |
| S23 | 1 | (ITO indium-tin-oxide) near10 AlGaAs near10 Zn and (light-emitting light adj emitting) adj diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:07 |
| S24 | 1 | (ITO indium-tin-oxide) near10 AlGaAs near10 (Si Ge Zn Mg Cd) and (light-emitting light adj emitting) adj diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:08 |
| S25 | 0 | (ITO indium-tin-oxide) near10 AlGaAs near10 heavily adj doped and (light-emitting light adj emitting) adj diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:08 |
| S26 | 0 | (ITO indium-tin-oxide) near10 AlGaAs near10 (n+ "N+" heavily adj doped) and (light-emitting light adj emitting) adj diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:09 |
| S27 | 0 | (ITO indium-tin-oxide) near10 AlGaAs near10 ("n.sub.+" "N.sub. +" heavily adj doped) and (light-emitting light adj emitting) adj diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:09 |
| S28 | 17 | (ITO indium-tin-oxide) near10 AlGaAs and (light-emitting light adj emitting) adj diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:20 |
| S29 | 4 | ohmic adj contact near10 (AlAs AlGaAs) near10 (ITO TCO transparent) and (light-emitting adj diode light adj emitting adj diode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:25 |
| S30 | 2 | ohmic adj contact near10 (AlAs AlGaAs) near10 (electrode) and (light-emitting adj diode light adj emitting adj diode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:30 |

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| S31 | 0 | ohmic adj contact near10 (AlAs AlGaAs) near10 (ITO TCO) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:31 |
| S32 | 0 | ohmic adj contact near10 (AlAs AlGaAs) near10 zinc adj oxide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:31 |
| S33 | 106 | ohmic adj contact near5 (AlAs AlGaAs) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:32 |
| S34 | 51 | ohmic adj contact near3 (AlAs AlGaAs) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:51 |
| S35 | 0 | ohmic adj contact near3 (AlAs AlGaAs) and exfoliat$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:43 |
| S36 | 0 | (adhesion adhesive) near10 (AlAs AlGaAs) near10 ohmic adj contact | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 20:51 |
| S37 | 5 | ohmic adj contact near3 (AlAs AlGaAs) and "10.sup.19"$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 21:27 |
| S38 | 53 | band adj gap near4 ohmic adj contact | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 21:54 |
| S39 | 27 | band adj gap near3 ITO | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 21:47 |
| S40 | 0 | direct adj gap near3 ohmic adj contact | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 21:49 |

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| S41 | 0 | direct adj gap near3 contact adj region | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 21:50 |
| S42 | 0 | direct adj2 gap near3 contact adj region | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 21:50 |
| S43 | 6 | contact adj resistance near4 band adj gap | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 22:00 |
| S44 | 0 | (p-type adj ito) near5 (band adj gap) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 22:06 |
| S45 | 0 | "Al.sub."$4"Ga.sub."$4As near10 band adj gap near10 (contact adj region ohmic adj contact) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 22:15 |
| S46 | 2 | "6236065".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 22:35 |
| S47 | 2 | "6495862".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 22:35 |
| S48 | 0 | "6495862".pn. and AlGaN | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 22:35 |
| S49 | 1 | "6495862".pn. and exfoliat$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 22:37 |
| S50 | 1 | "6495862".pn. and exfoliat$3 and (AlGaAs AlGaN Al aluminum) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 22:50 |

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| S51 | 690 | contact adj (region layer) near6 (impurity adj concentration) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 22:51 |
| S52 | 22 | contact adj (region layer) near4 (impurity adj concentration) and transparent adj electrode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/30 22:51 |
| S53 | 0 | direct adj2 band adj gap near10 (ohmic adj contact contact adj region) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/31 06:43 |
| S54 | 6 | "Al.sub."$4"Ga.sub."$4As near10 (ohmic adj contact contact adj region) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/05/31 06:43 |
| S55 | 10 | (US-20020096688-$ or US-20020110940-$ or US-20040197981-$ or US-20040227151-$).did. or (US-5770489-$ or US-6055262-$ or US-6856087-$ or US-6867426-$).did. or (JP-2002226846-$).did. or (JP-2002226846-$).did. | US-PGPUB; USPAT; JPO; DERWENT | OR | OFF | 2005/05/31 07:31 |
| S56 | 3 | S55 and Zn | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/31 07:19 |
| S57 | 2 | S55 and Mg | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/31 07:20 |
| S58 | 9 | "6495862" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/31 07:21 |
| S59 | 2 | ("6495862").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/31 07:21 |

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| S60 | 11 | (US-20020096688-$ or US-20020110940-$ or US-20040197981-$ or US-20040227151-$).did. or (US-5770489-$ or US-6055262-$ or US-6856087-$ or US-6867426-$ or US-6495862-$).did. or (JP-2002226846-$).did. or (JP-2002226846-$).did. | US-PGPUB; USPAT; JPO; DERWENT | OR | OFF | 2005/05/31 07:31 |
| S61 | 1 | S60 and autodoped | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/31 07:33 |
| S62 | 75 | autodoped | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/31 07:33 |
| S63 | 35 | autodoped.ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/31 07:33 |
| S64 | 20 | jp-1130810$-$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/01 15:09 |
| S65 | 2 | jp-11307810$-$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/01 15:09 |
| S66 | 2 | jp-2002344017$-$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/01 15:10 |
| S67 | 2 | ("6350997").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/01 15:10 |
| S68 | 2 | "6350997".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 16:28 |

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| S69 | 3 | "116324".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/08 09:42 |
| S70 | 1 | (US-20040227151-$).did. | US-PGPUB | OR | OFF | 2005/11/13 18:03 |
| S71 | 1 | S70 and prevent$3 near6 concentrat$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/11/13 18:06 |
| S72 | 2 | ("5869849").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/11/13 18:10 |
| S73 | 8 | JP-2002232005$-$.did. JP-2000174344$-$.did. JP-08097467$-$.did. JP-2000312028$-$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 18:38 |
| S74 | 2 | jp-2003158887$-$.did. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 19:11 |
| S75 | 418 | graded near3 clad$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/11/13 19:34 |
| S76 | 6 | (double graded) near3 clad$4 and (indium adj tin adj oxide ito) and (zn zinc) near2 dop$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 19:42 |
| S77 | 10 | (double graded) near2 active and (indium adj tin adj oxide ito) and (zn zinc) near2 dop$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 19:54 |
| S78 | 10 | (double graded bi-layer) near2 active and (indium adj tin adj oxide ito) and (zn zinc) near2 dop$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 19:54 |
| S79 | 16 | (double graded bi-layer laminate) near2 active and (indium adj tin adj oxide ito) and (zn zinc) near2 dop$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 19:55 |

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| S80 | 3 | (double graded bi-layer laminate) near2 active and (indium adj tin adj oxide ito) and (zn zinc) near2 dop$3 and AlGaInP | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 20:29 |
| S81 | 0 | "5869849".pn. and (mqw multiple ad adj "well") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 20:30 |
| S82 | 1854 | (AlGaInP GaAlInP InGaAlP InAlGaP) and (mqw multiple ad adj "well") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 20:31 |
| S83 | 348 | (AlGaInP GaAlInP InGaAlP InAlGaP) with (mqw multiple ad adj "well") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 20:31 |
| S84 | 29 | (AlGaInP GaAlInP InGaAlP InAlGaP) with (mqw multiple ad adj "well") and ito | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 20:31 |
| S85 | 6 | (AlGaInP GaAlInP InGaAlP InAlGaP) with (mqw multiple ad adj "well") and ito and (zn zinc) near3 dop$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 21:03 |
| S86 | 134 | (mqw multiple ad adj "well") with quantum adj2 efficiency | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 21:04 |
| S87 | 0 | (mqw multiple ad adj "well") with quantum adj2 efficiency with light-emitting adj diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 21:04 |
| S88 | 14 | (mqw multiple ad adj "well") with quantum adj2 efficiency with (light adj emitting light-emitting) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 21:05 |
| S89 | 3 | (mqw multiple adj "well") with quantum adj2 efficiency with (light adj emitting light-emitting) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 21:05 |

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| S90 | 4 | (mqw multiple adj quantum adj "well") with quantum adj2 efficiency with (light adj emitting light-emitting) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/13 21:05 |